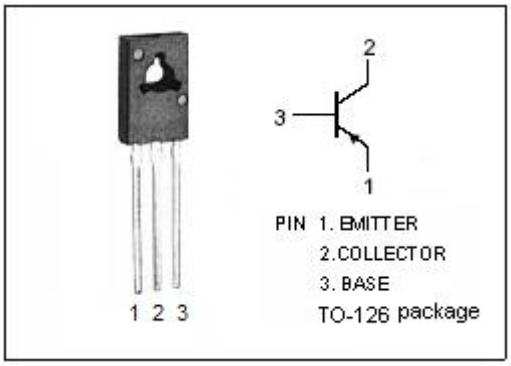
isc Silicon PNP Power Transistor — KSA1381

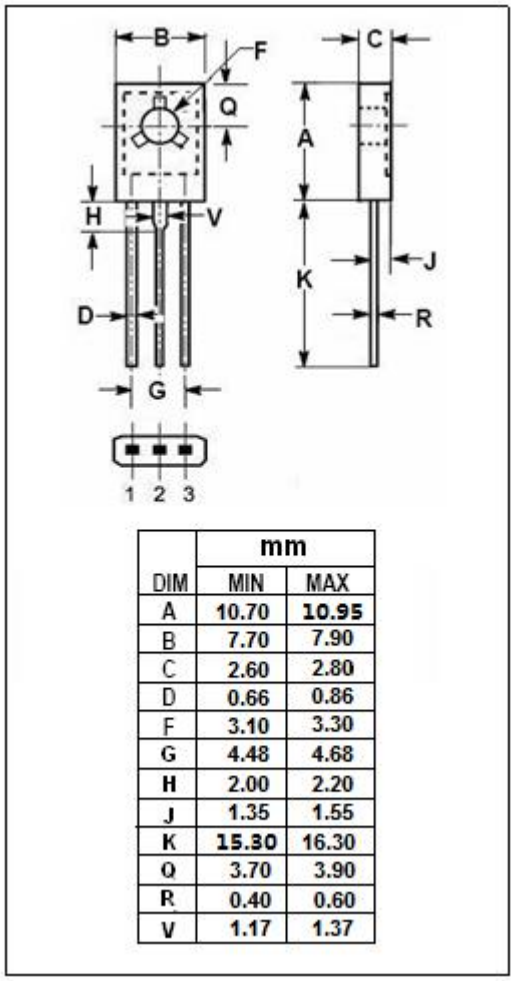


DESCRIPTION

- Low Collector Saturation Voltage
- High voltage
- High speed switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- CRT display,video output



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-300	V
V_{CEO}	Collector-Emitter Voltage	-300	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.1	A
P_C	Total Power Dissipation @ Ta=25℃	1.2	w
	Total Power Dissipation @ T_C=25℃	7	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -20mA; I_B= -2mA			-0.6	V
$V_{BE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -20mA; I_B= -2mA			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -200V; I_E= 0			-0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-0.1	μA
h_{FE}	DC Current Gain	I_C= -10mA ; V_{CE}= -10V	40		320	

◆ **h_{FE} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320